

*b1 bmd. sug D2 emb.*  
wherein a composition ratio of Al and In in said first layer is changed continuously or intermittently in a direction toward the second layer side from the buffer layer side so that a lattice constant of said first layer in a face brought into contact with said second layer becomes substantially equal to a lattice constant of said second layer.

---

*C2 sug D2*  
6. (Amended) A group III nitride compound semiconductor device according to claim 3, wherein the composition ratio of Al and In in said first layer is changed continuously or intermittently in the direction toward the second layer side from the buffer layer side so that a band gap of said first layer in a face brought into contact with said second layer becomes wider than a band gap of said second layer.

---

Please add claims 7 and 8 as follows:

---

*C2*  
7. A group III nitride compound semiconductor device according to claim 1, wherein said buffer layer comprises  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 \leq x \leq 1$ ).

8. A group III nitride compound semiconductor device according to claim 3, wherein said buffer layer comprises  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 \leq x \leq 1$ ).

---

#### REMARKS

Claims 1, 3, and 5-8 are pending in the application. This Amendment amends claims 3 and 6, cancels claim 4, and adds claims 7 and 8. No new matter is added to amended claims 3 and 6, or to new claims 7 and 8. Independent claim 3 is amended to incorporate the subject matter of dependent claim 4, while claim 6 is amended merely to change its dependency from canceled claim 4 to claim 3. Notwithstanding any claim amendments of the present Amendment or those amendments that may be made later during prosecution, Applicant's intent is to encompass equivalents of all claim elements. Reconsideration in view of the foregoing